

P/N: YZPST-30SQ045

Plastic SchottkyBarrier Rectifier

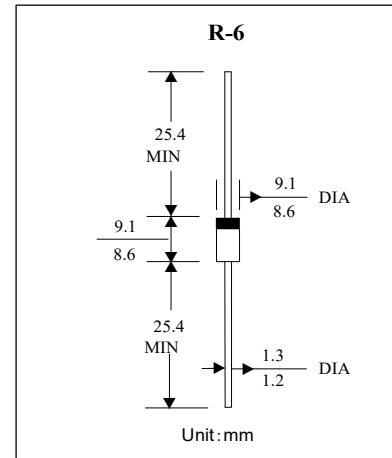
塑封肖特基二极管

Features

- Metal silicon rectifie, majority carrier conduction
- Guard ring for transient protection
- Low pwer loss, high efficiency
- High current capability low VF
- High surge capacity
- Plastic package has UL flammability classification 94 V-0

Mechanical Data

- Cases: JEDEC R-6 molded plastic
- Polarity: Color band cenotes cathode
- Weight: 0.07 ounces 2.1 grams
- Mounting position: Any



芯片尺寸 Chip size: 150mil
芯片类型: 平面
Chip type: flat surface

极限值和电参数 TA = 25°C 除非另有规定。

Maximum Ratings & Electrical Characteristics

Ratings at 25°C ambient temperature unless otherwise specified.

Single phase, half wave, 60Hz, resistive or inductive load.

For capacitive load, derate current by 20%

	符号 Symbols	30SQ045	单位 Unit
最大峰值反向电压 Maximum repetitive peak reverse voltage	V_{RRM}	45	V
最大反向有效值电压 Maximum RMS voltage	$V_{R(RMS)}$	31.5	V
最大直流阻断电压 Maximum DC blocking voltage	V_{DC}	45	V
最大正向电压降 @IF = 30A Maximum forward voltage	V_F	0.55	V
最大正向平均整流电流 Maximum average forward rectified current	$I_{F(AV)}$	30	A
正向峰值浪涌电流 8.3ms单一正弦半波 Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	I_{FSM}	300	A
最大反向漏电流 @TA = 25°C Maximum reverse current @TA = 100°C	I_R	0.2 10	mA
典型热阻 Typical thermal resistance	$R_{\theta JA}$	3.0	°C/W
存储温度 Storage temperature range	T_{STG}	-55 --- +150	°C
工作温度 Junction temperature range at reduced reverse voltage in DC forward mode $V_R \leq 80\% V_{RRM}$ $V_R \leq 50\% V_{RRM}$	T_J	-55 --- +150 ≤ 175 ≤ 200	°C

特性曲线 Characteristic Curves

